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(72) Inventors; and

(75) Inventors/Applicants (for US only): **MISRA, Ashutosh** [IN/US]; 2425 Hunters Run Drive, Plano, TX 75025 (US). **FISHER, Matthew** [US/US]; 417 St. Andrews Drive, Allen, TX 75002 (US). **JURCIK, Benjamin** [US/US]; 2415 Canyon Creek Drive, Richardson, TX 75080 (US). **DUSSARRAT, Christian** [FR/JP]; Tsukuba-Matsushiro 4-2-1 #204, 4-15-2, Matsushiro, Tsukuba-Shi, Ibaraki 305-0035 (FR). **TSUKADA, Eri** [JP/JP]; Amour Liberte 18, 306, 2-13-3 Matsushiro, Tsukuba, Ibaraki 305-0035 (JP). **GIRARD, Jean-Marc** [FR/FR]; 12, rue Michel Chasles, F-75012 Paris (FR).

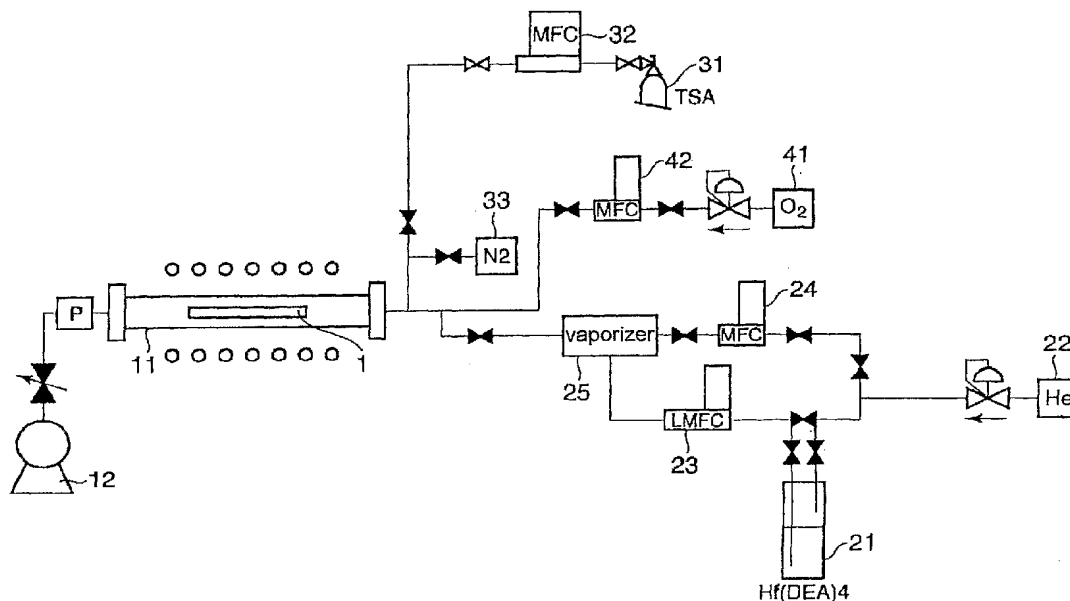
(74) Agents: **VESIN, Jacques** et al.; c/o L'air Liquide S.A., Direction de la Propriété Intellectuelle, 75, quai d'Orsay, F-75321 Paris Cedex 07 (FR).

(71) Applicant (for all designated States except US): **L'AIR LIQUIDE, SOCIETE ANONYME A DIRECTOIRE ET CONSEIL DE SURVEILLANCE POUR L'ETUDE ET L'EXPLOITATION DES PROCEDES GEORGES CLAUDE** [FR/FR]; 75, quai d'Orsay, F-75321 Paris Cedex 07 (FR).

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[Continued on next page]

(54) Title: METHOD FOR FORMING DIELECTRIC OR METALLIC FILMS



(57) Abstract: Method for producing a metal silicon (oxy)nitride by introducing a carbon-free silicon source (for example,  $(\text{SiH}_3)_3\text{N}$ ), a metal precursor with the general formula  $\text{MX}_n$  (for example,  $\text{Hf}(\text{NEt}_2)_4$ ), and an oxidizing agent (for example,  $\text{O}_2$ ) into a CVD chamber and reacting same at the surface of a substrate.  $\text{MsiN}$ ,  $\text{MSiO}$  and/or  $\text{MSiON}$  films may be obtained. These films are useful as high k dielectrics films.

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